onsemi

General Purpose Transistor

PNP Silicon

MMBT2907AWT1G, NSVMMBT2907AWT1G

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

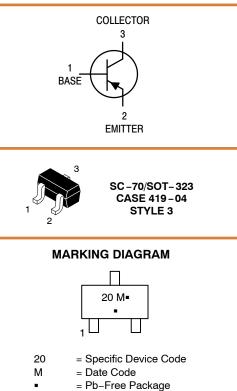
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-60	Vdc
Collector - Base Voltage	V _{CBO}	-60	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C	P _D	150	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T _J , T _{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.



= = FD-I lee Fackage

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2907AWT1G	SC-70 (Pb-Free)	3000 Tape & Reel
NSVMMBT2907AWT1G	SC-70 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 2) $(I_C = -10 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-60	_	Vdc
Collector – Base Breakdown Voltage $(I_C = -10 \ \mu Adc, I_E = 0)$	V _(BR) CBO	-60	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	_	Vdc
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _{BL}	-	-50	nAdc
Collector Cutoff Current ($V_{CE} = -30$ Vdc, $V_{EB(off)} = -0.5$ Vdc)	I _{CEX}	-	-50	nAdc
ON CHARACTERISTICS ⁽³⁾				•
DC Current Gain (Note 2) ($I_C = -0.1 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$) ($I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$) ($I_C = -10 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$) ($I_C = -150 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$) ($I_C = -500 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}$)	H _{FE}	75 100 100 100 50	- - 340 -	_
Collector – Emitter Saturation Voltage (Note 2) ($I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc}$) ($I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc}$)	V _{CE(sat)}	-	-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 2) ($I_C = -150 \text{ mAdc}$, $I_B = -15 \text{ mAdc}$) ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)	V _{BE(sat)}	-	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product ($I_C = -50 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, f = 100 MHz)	f _T	200	_	MHz
Output Capacitance ($V_{CB} = -10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	30	pF
SWITCHING CHARACTERISTICS	- · · ·			

Turn-On Time		t _{on}	-	45	
Delay Time	(V _{CC} = −30 Vdc, I _C = −150 mAdc, I _{B1} = −15 mAdc)	t _d	-	10	
Rise Time		t _r	-	40	20
Storage Time		ts	-	80	ns
Fall Time	(V _{CC} = -6.0 Vdc, I _C = -150 mAdc, I _{B1} = I _{B2} = 15 mAdc)	t _f	-	30	
Turn-Off Time		t _{off}	-	100	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

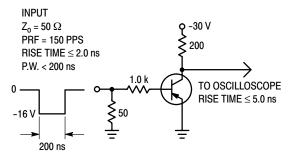


Figure 1. Delay and Rise Time Test Circuit

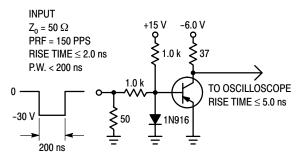
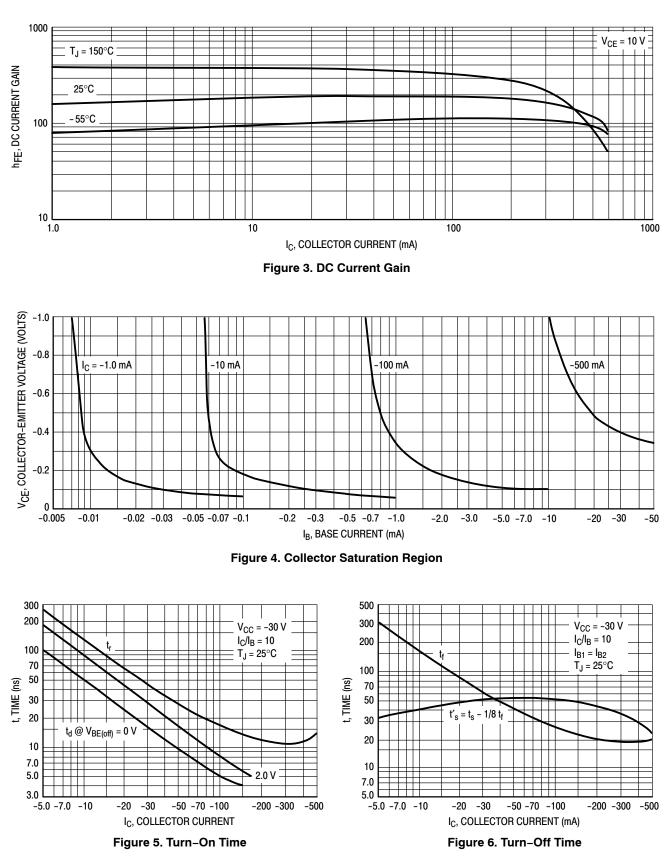


Figure 2. Storage and Fall Time Test Circuit

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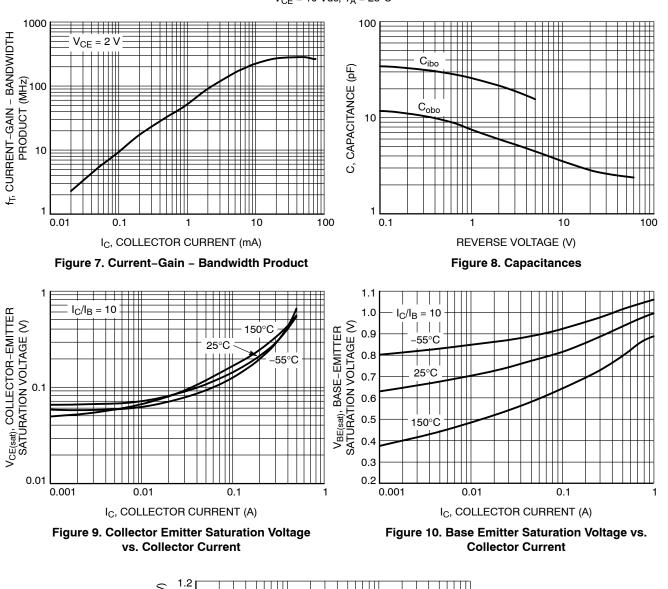
TYPICAL CHARACTERISTICS

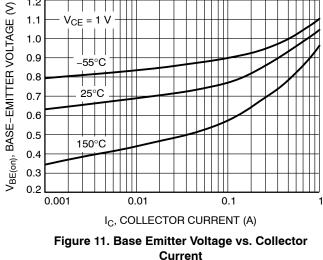


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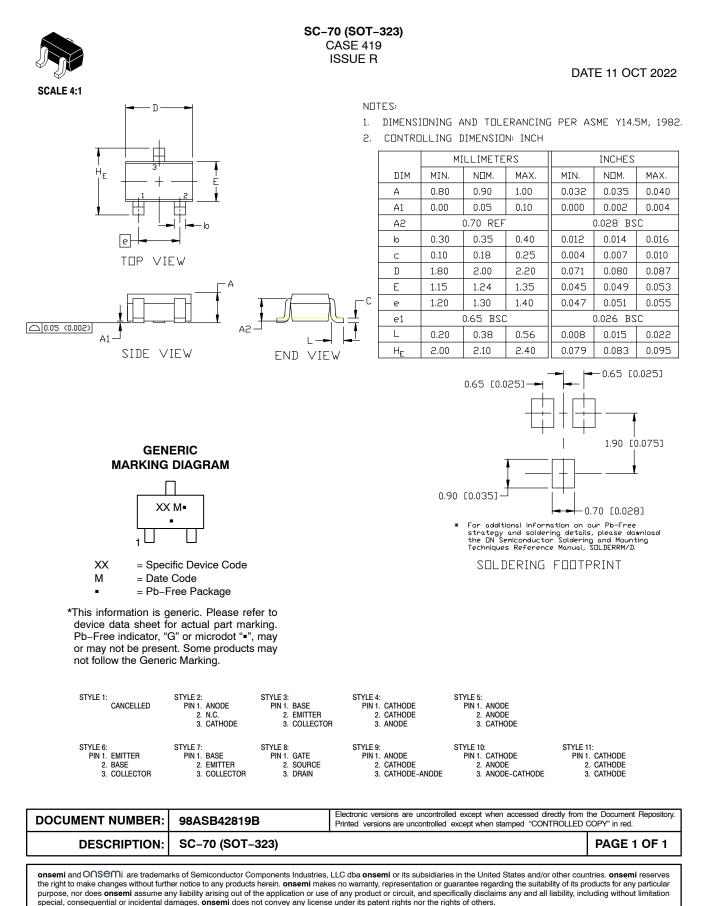
 V_{CE} = 10 Vdc, T_A = 25°C





MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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